

# MA6X128

Silicon epitaxial planar type

For switching circuits

### ■ Features

- Four-element contained in one package, allowing high-density mounting
- Centrosymmetrical wiring, allowing to free from the taping direction
- The mirror image wiring of (MA6X123)
- Short reverse recovery time  $t_{rr}$
- Small terminal capacitance,  $C_t$
- High breakdown voltage ( $V_R = 80$  V)

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	80	V
Peak reverse voltage	$V_{RM}$	80	V
Forward current (DC)*1	$I_F$	100	mA
Peak forward current*1	$I_{FM}$	225	mA
Non-repetitive peak forward surge current*1,2	$I_{FSM}$	500	mA
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \*1: Value for single diode

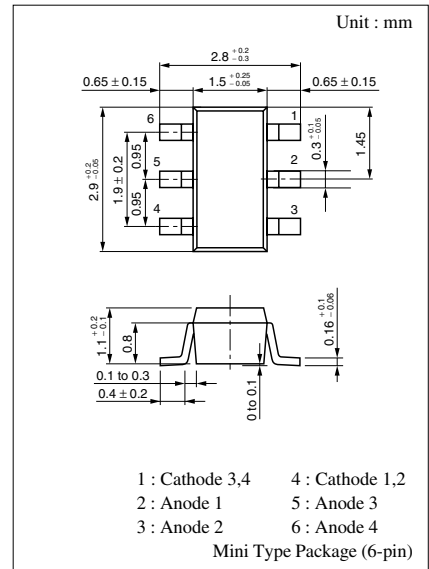
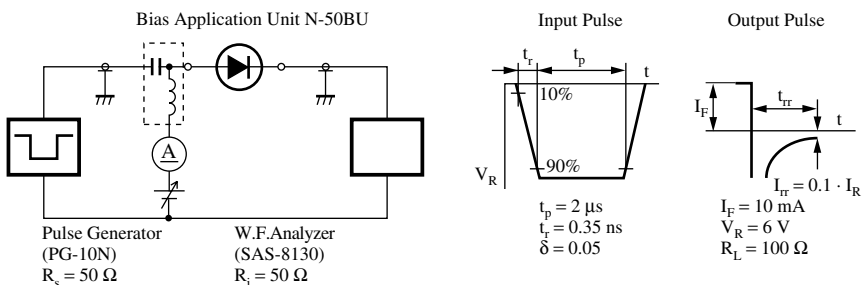
\*2:  $t = 1$  s

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 75$ V			100	nA
Forward voltage (DC)	$V_F$	$I_F = 100$ mA			1.2	V
Reverse voltage (DC)	$V_R$	$I_R = 100$ $\mu\text{A}$	80			V
Terminal capacitance	$C_t$	$V_R = 0$ V, $f = 1$ MHz			2	pF
Reverse recovery time*	$t_{rr}$	$I_F = 10$ mA, $V_R = 6$ V $I_{tr} = 0.1 \cdot I_R$ , $R_L = 100$ $\Omega$			3	ns

Note) 1. Rated input/output frequency: 100 MHz

2. \*:  $t_{rr}$  measuring circuit



Marking Symbol: M2V

Internal Connection

